

KSD1691

Feature

- Low Collector-Emtter Saturation Voltage & Large Collector Current
- High Power Dissipation: P_C = 1.3W (T_a=25°C)
 Complementary to KSB1151



NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings T_C=25°C unless otherwise noted

| Symbol | Parameter | Value | Units |
|------------------|--|------------|-------|
| V _{CBO} | Collector-Base Voltage | 60 | V |
| V _{CEO} | Collector-Emitter Voltage | 60 | V |
| V _{EBO} | Emitter-Base Voltage | 7 | V |
| I _C | Collector Current (DC) | 5 | Α |
| I _{CP} | *Collector Current (Pulse) | 8 | Α |
| I _B | Base Current (DC) | 1 | Α |
| P _C | Collector Dissipation (T _a =25°C) | 1.3 | W |
| P _C | Collector Dissipation (T _C =25°C) | 20 | W |
| TJ | Junction Temperature | 150 | °C |
| T _{STG} | Storage Temperature | - 55 ~ 150 | °C |

* PW≤10ms, duty Cycle≤50%

Electrical Characteristics $T_C=25^{\circ}C$ unless otherwise noted

| Symbol | Parameter | Test Condition | Min. | Тур. | Max. | Units |
|-----------------------|---------------------------------------|------------------------------|------|------|------|-------|
| I _{CBO} | Collector Cut-off Current | $V_{CB} = 50V, I_{E} = 0$ | | | 10 | μΑ |
| I _{EBO} | Emitter Cut-off Current | $V_{EB} = 7V, I_{C} = 0$ | | | 10 | μΑ |
| h _{FE1} | *DC Current Gain | $V_{CE} = 1V, I_{C} = 0.1A$ | 60 | | | |
| h_{FE2} | | $V_{CE} = 1V$, $I_{C} = 2A$ | 100 | | 400 | |
| h_{FE3} | | $V_{CE} = 1V$, $I_C = 5A$ | 50 | | | |
| V _{CE} (sat) | *Collector-Emitter Saturation Voltage | $I_C = 2A, I_B = 0.2A$ | | 0.1 | 0.3 | V |
| V _{BE} (sat) | *Base-Emitter Saturation Voltage | $I_C = 2A, I_B = 0.2A$ | | 0.9 | 1.2 | V |
| t _{ON} | Turn ON Time | $V_{CC} = 10V, I_{C} = 2A$ | | 0.2 | 1 | μs |
| t _{STG} | Storage Time | $I_{B1} = -I_{B2} = 0.2A$ | | 1.1 | 2.5 | μs |
| t _F | Fall Time | $R_L = 5\Omega$ | | 0.2 | 1 | μs |

^{*} Pulse test: PW≤50µs, duty Cycle≤2% Pulsed

h_{FE} Classificntion

| Classification | 0 | Υ | G | |
|-------------------|-----------|-----------|-----------|--|
| h _{FE 2} | 100 ~ 200 | 160 ~ 320 | 200 ~ 400 | |

Typical Characteristics

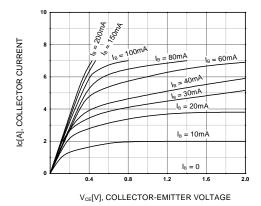


Figure 1. Static Characteristic

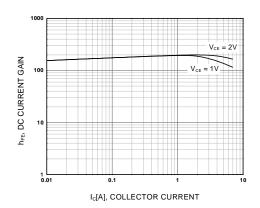


Figure 2. DC current Gain

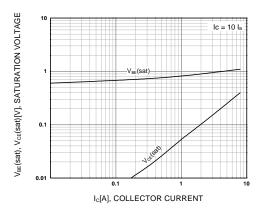


Figure 3. Collector-Emitter Saturation Voltage Base-Emitter Saturation Voltage

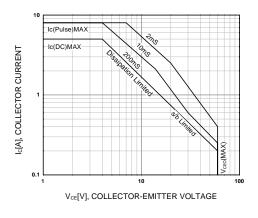


Figure 4. Forward Bias Safe Operating Area

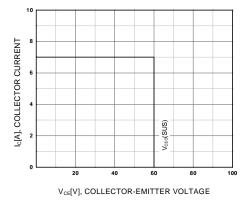


Figure 5. Reverse Bias Safe Operating Area

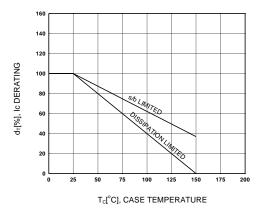


Figure 6. Derating Curve of Safe Operating Areas

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Typical Characteristics (Continued)

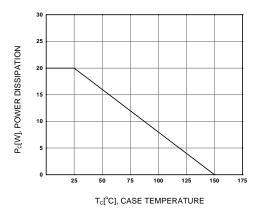
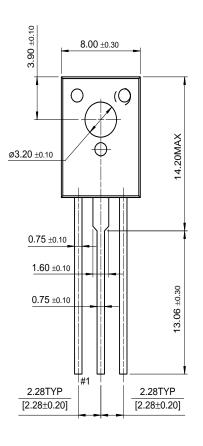


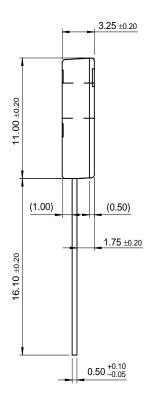
Figure 7. Power Derating

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Package Demensions

TO-126





Dimensions in Millimeters

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